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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
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Complete if Known

Application Number	10/789,042
Filing Date	February 27, 2004
First Named Inventor	Ahn, Kie
Group Art Unit	2815
Examiner Name	Wilson, Allan Richards

Attorney Docket No: 1303.050US2

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EXAMINER

*[Handwritten signature]*

DATE CONSIDERED 8/31/04

Substitute Disclosure Statement Form (PTO-1449)

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First Named Inventor Ahn, Kie  
Group Art Unit 2815  
Examiner Name ~~Wilson, Allen~~ Richards

Sheet 2 of 4

Attorney Docket No: 1303.050US2

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EXAMINER

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First Named Inventor Ahn, Kie  
Group Art Unit 2815  
Examiner Name Wilson, Allen R. Richards

Sheet 3 of 4

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	Group Art Unit	2815
	Examiner Name	<del>Wilson</del> , <u>Atlan Richards</u>
Sheet 4 of 4	Attorney Docket No: 1303.050US2	

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T <sup>2</sup>
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*Atlan Richards*

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